AMENDMENTS TO THE CLAIMS

1. (Previously presented) A semiconductor device, comprising:

a semiconductor substrate; and

a conductive layer formed on said semiconductor substrate and including polycrystals, said conductive layer including in its surface a recess caused by a crystal grain boundary and having side walls formed such that a distance therebetween becomes small as closer to said semiconductor substrate, wherein said conductive layer includes:

a first conductive layer having a substantially planar upper surface, formed on said semiconductor substrate and including a polycrystal having a first average grain size;

a second conductive layer formed on said first conductive layer, including a polycrystal having a second average grain size greater than said first average grain size and having said recess; and

said recess is formed directly over the substantially planar upper surface of the first conductive layer.

2. (Cancelled)

3. (Original) The semiconductor device according to claim 1, further comprising a thin film layer formed on said conductive layer and having a material different from that of said conductive layer.

4. (Original) The semiconductor device according to claim 1, wherein said conductive layer includes aluminum.

5. (Original) The semiconductor device according to claim 1, further comprising an insulating layer formed on said semiconductor substrate and a barrier layer formed on said insulating layer, said conductive layer being formed on said barrier layer.

6-20. (Cancelled)